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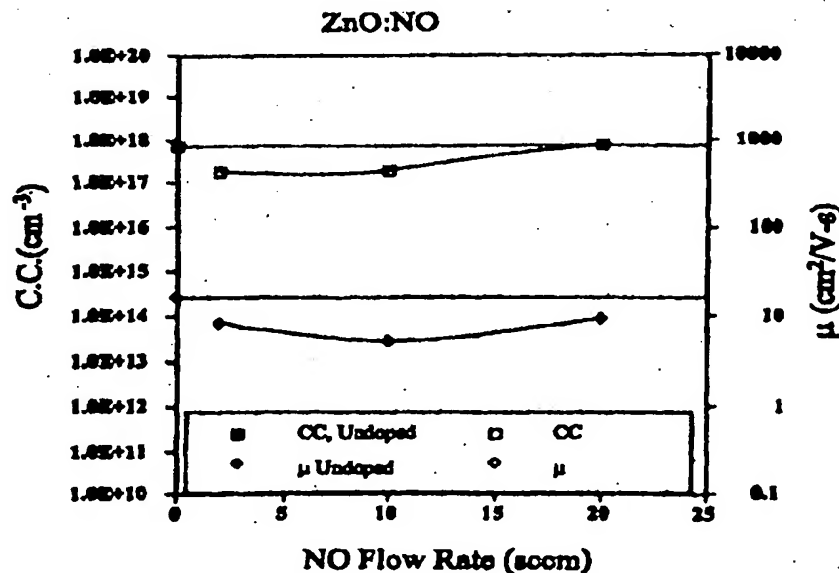
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WEST RESEARCH INSTITUTE [US/US]; 425 Volker
Boulevard, Kansas City, MO 64110 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): LI, Xiaonan
[US/US]; 1591 Prouty Drive, Evergreen, CO 80439
(US). YAN, Yanfa [CN/US]; 11888 W. Aqueduct Drive,Littleton, CO 80127 (US). COUTTS, Timothy, J.
[US/US]; 1229 Pomegranate lane, Golden, CO 80401
(US). GESSERT, Timothy, A. [US/US]; 29801 Kennedy
Gulch Road, Conifer, CO 80433 (US). DEHART, Clay,
M. [US/US]; 4615 west 112th Court, Westminster, CO
80031 (US).(74) Agents: WHITE, Paul, J. et al.; National Renewable En-
ergy Laboratory, 1617 Cole Boulevard, Golden, CO 80401
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(54) Title: METHOD FOR PRODUCING HIGH CARRIER CONCENTRATION P-TYPE TRANSPARENT CONDUCTING OX-
IDES

(57) Abstract: A method for producing transparent p-type conducting oxide films without co-doping plasma enhancement or high temperature comprising: a) introducing a dialkyl metal at ambient temperature and a saturated pressure in a carrier gas into a low pressure deposition chamber; and b) introducing NO alone or with an oxidizer into the chamber under an environment sufficient to produce a metal-rich condition to enable NO decomposition and atomic nitrogen incorporation into the formed transparent metal conducting oxide.

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